

## SAMYANG ELECTRONICS MURF1620CT --- MURF1660CT

### SUPER FAST RECTIFIERS

#### FEATURES

- $\diamondsuit {\sf M}{\sf etal}{\sf -}{\sf semiconductor}$  junction with guard ring
- $\bigcirc$  Epitaxial construction
- $\bigotimes$  Low forward voltage drop,low switching losses
- $\bigcirc$  High surge capability
- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- $\bigcirc$  The plastic material carries U/L recognition 94V-0

#### MECHANICAL DATA

- - MIL-STD-750,Method 2026
- ◇Polarity: As marked
- ♦ Weight: 0.08ounces, 2.24 grams

#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

	Symbols	MURF 1620CT	MURF 1640CT	MURF 1660CT	Units
Maximum repetitive peak reverse voltage	Vrrm	200	400	600	Volts
Maximum RMS voltage	Vrms	140	280	420	Volts
Maximum DC blocking voltage	Vdc	200	400	600	Volts
Maximum average forwardPer legrectified current(see Fig.1)Total device	l(AV)	8.0 16.0			Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	IFSM	100			Amps
Maximum instantaneous forward voltage at 10.0 A(Note 1 )	VF	0.975	1.3	1.7	Volts
Maximum instantaneous reverse $T_{A} = 25^{\circ}C$	lr -	5	10		
current at rated DC blocking voltage(Note 1) $T_{A} = 125^{\circ}C$		500			– uA
Maximum Reverse Recovery Time (Note 2)	Trr	35			ns
Typical thermal resistance (Note 3)	R <sub>θ</sub> JC	3.0			°C/W
Operating junction temperature range	TJ	-65 to+175			°C
Storage temperature range	Tstg	-65 to+175			°C

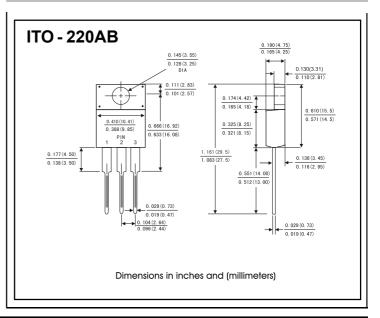
NOTE: 1. Pulse test:300us pulse width,1% duty cycle.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

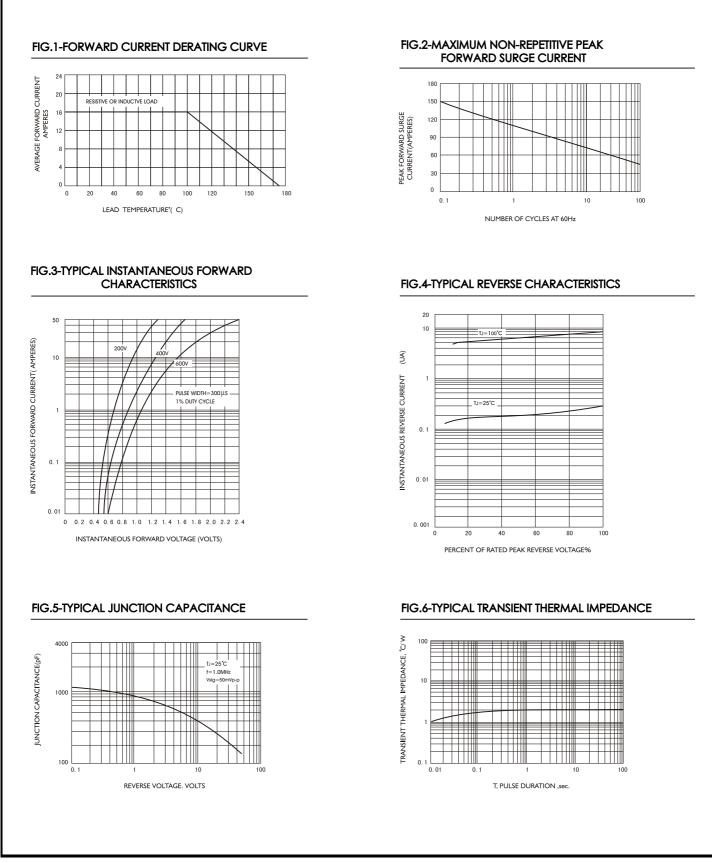
3. Thermal resistance junction to ambient

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### VOLTAGE RANGE: 200 --- 600 V CURRENT: 16.0A



# **RATINGS AND CHARACTERISTIC CURVES**



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